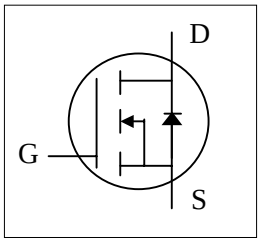
N-CHANNEL ENHANCEMENT MODE POWER MOSFET

PRODUCT SUMMARY

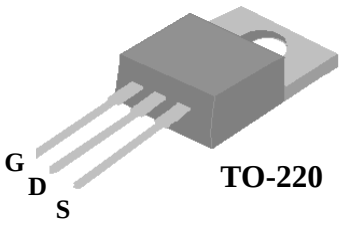
Lower On-resistance
Fast Switching Characteristic
Simple Drive Requirement
RoHS Compliant



BV_{DSS}	650V
$R_{DS(ON)}$	1Ω
I_D	10A

DESCRIPTION

The TO-220 package is universally preferred for all commercial-industrial applications. The device is suited for DC-DC ,AC-DC converters for power applications.



Pb-free; RoHS-compliant

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	650	V
V_{GS}	Gate-Source Voltage	±30	V
I_D@T_C=25℃	Continuous Drain Current, V_{GS} @ 10V	10	A
I_D@T_C=100℃	Continuous Drain Current, V_{GS} @ 10V	4.4	A
I_{DM}	Pulsed Drain Current[1]	18	A
P_D@T_C=25℃	Total Power Dissipation	104	W
	Linear Derating Factor	0.8	W/℃
I_{AR}	Avalanche Current	10	A
T_{STG}	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 150	℃

THERMAL DATA

Symbol	Parameter		Value	Units
Rthj-c	Thermal Resistance Junction-case	Max.	1.2	℃/W
Rthj-a	Thermal Resistance Junction-ambient	Max.	62	℃/W

ELECTRICAL CHARACTERISTICS @Tj=25°C(unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V, I_D=1mA	650	-	-	V
$\Delta BV_{DSS}/\Delta T_j$	Breakdown Voltage Temperature Coefficient	Reference to 25℃, I_D=1mA	-	0.6	-	V/℃
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=10V, I_D=3.5A	-	-	1	Ω
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=250uA	2	-	4	V
g_{fs}	Forward Transconductance	V_{DS}=10V, I_D=3.5A	-	4.5	-	S
I_{DSS}	Drain-Source Leakage Current (T_j=25°C)	V_{DS}=600V, V_{GS}=0V	-	-	10	uA
	Drain-Source Leakage Current (T_j=150°C)	V_{DS}=480V, V_{GS}=0V	-	-	100	uA
I_{GSS}	Gate-Source Leakage	V_{GS}=±30V	-	-	±100	nA
Q_g	Total Gate Charge[3]	I_D=10A	-	53	85	nC
Q_{gs}	Gate-Source Charge	V_{DS}=520V	-	10	-	nC
Q_{gd}	Gate-Drain ("Miller") Charge	V_{GS}=10V	-	15	-	nC
$t_{d(on)}$	Turn-on Delay Time[3]	V_{DD}=320V	-	16	-	ns
t_r	Rise Time	I_D=10A	-	20	-	ns
$t_{d(off)}$	Turn-off Delay Time	R_G=10Ω,V_{GS}=10V	-	82	-	ns
t_f	Fall Time	R_D=32Ω	-	36	-	ns
C_{iss}	Input Capacitance	V_{GS}=0V	-	2770	4430	pF
C_{oss}	Output Capacitance	V_{DS}=15V	-	320	-	pF
C_{rss}	Reverse Transfer Capacitance	f=1.0MHz	-	8	-	pF

Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V_{SD}	Forward On Voltage[3]	I_S=10A, V_{GS}=0V	-	-	1.5	V
t_{rr}	Reverse Recovery Time[3]	I_S=10A, V_{GS}=0V,	-	610	-	ns
Q_{rr}	Reverse Recovery Charge	dI/dt=100A/μs	-	8.64	-	μC

Notes:

1.Pulse width limited by safe operating area.

2.Starting T_j=25°C , V_{DD}=50V , L=1.2mH , R_G=25Ω , I_{AS}=10A.

3.Pulse width ≤300us , duty cycle ≤2%.

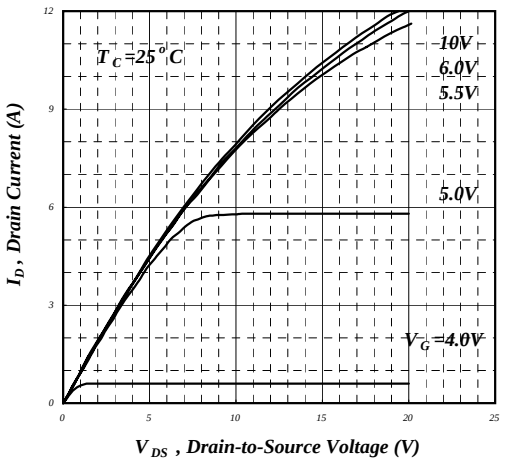


Fig 1. Typical Output Characteristics

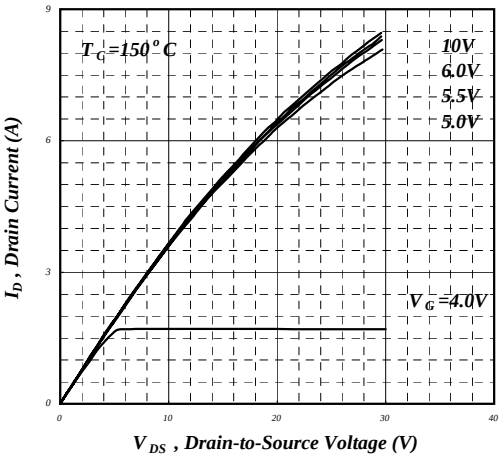


Fig 2. Typical Output Characteristics

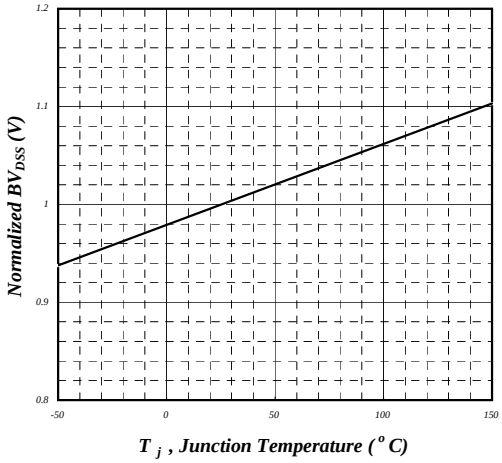


Fig 3. On-Resistance v.s. Gate Voltage

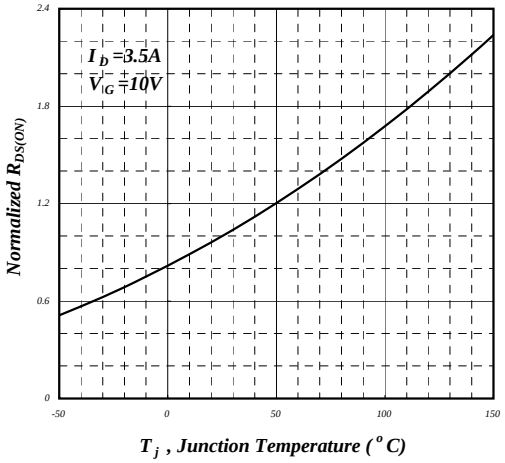


Fig 4. Normalized On-Resistance v.s. Junction Temperature

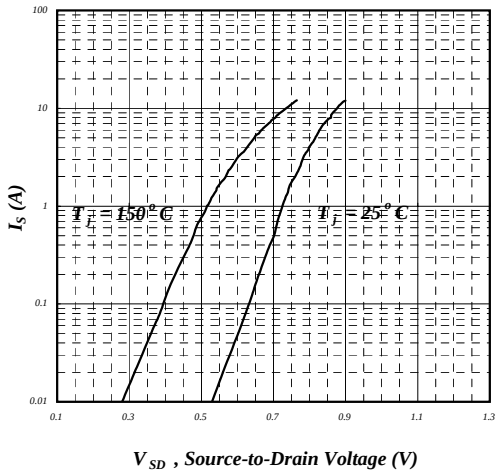


Fig 5. Forward Characteristic of Reverse Diode

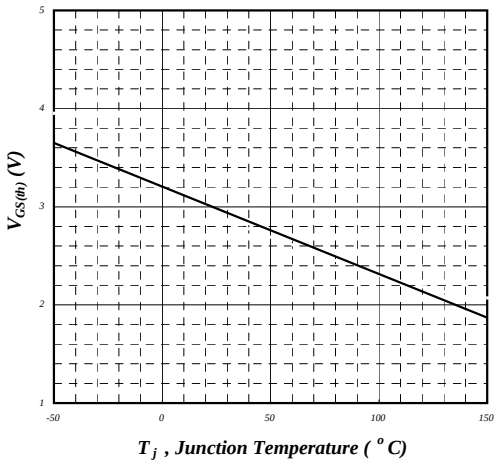


Fig 6. Gate Threshold Voltage v.s. Junction Temperature

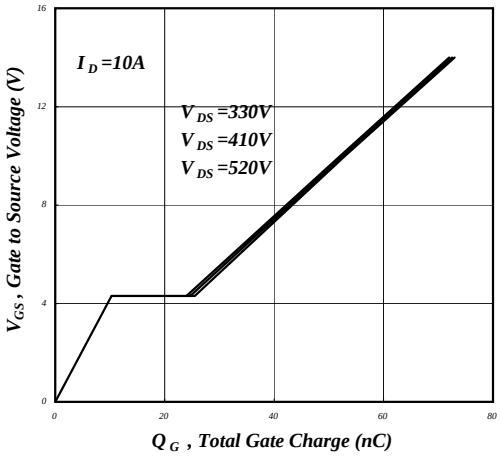


Fig 7. Gate Charge Characteristics

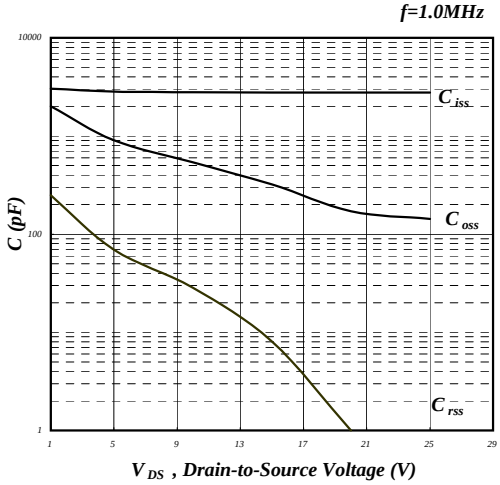


Fig 8. Typical Capacitance Characteristics

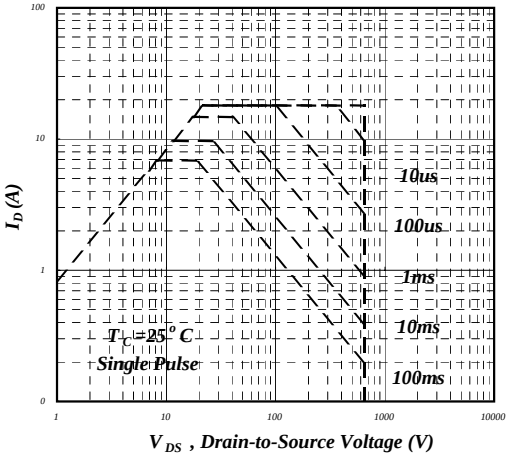


Fig 9. Maximum Safe Operating Area

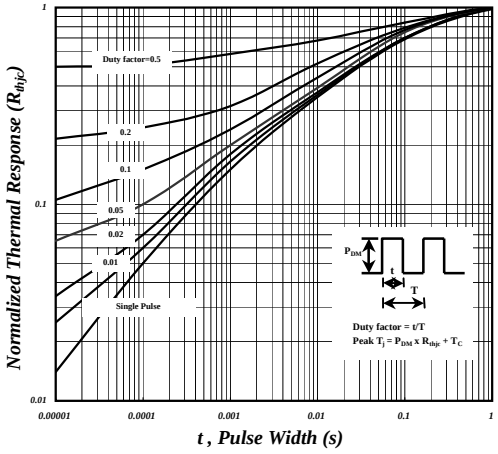


Fig 10. Effective Transient Thermal Impedance

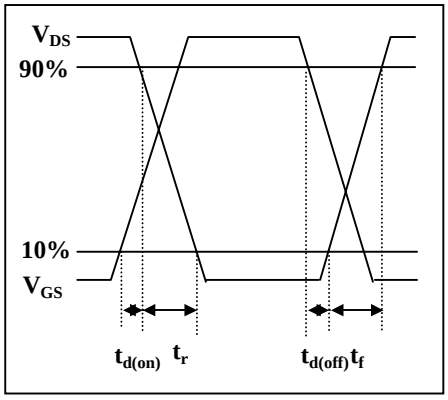


Fig 11. Switching Time Waveform

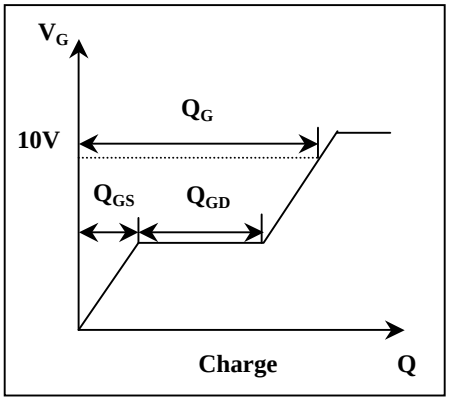


Fig 12. Gate Charge Waveform

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